
2SK522

Silicon N-Channel Junction FET

HITACHI

Application

VHF amplifier, Mixer, local oscillator

Outline

SPAK



- 1. Gate
- 2. Source
- 3. Drain

2SK522

Absolute Maximum Ratings (Ta = 25°C)

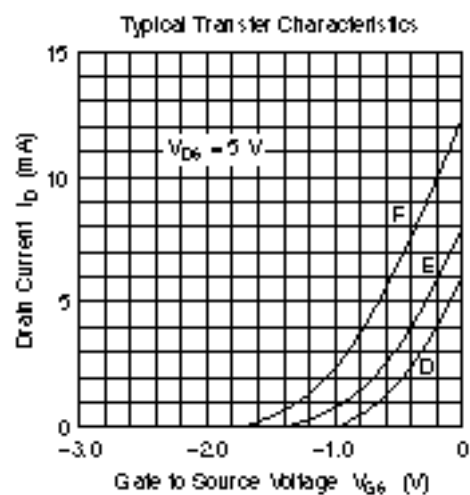
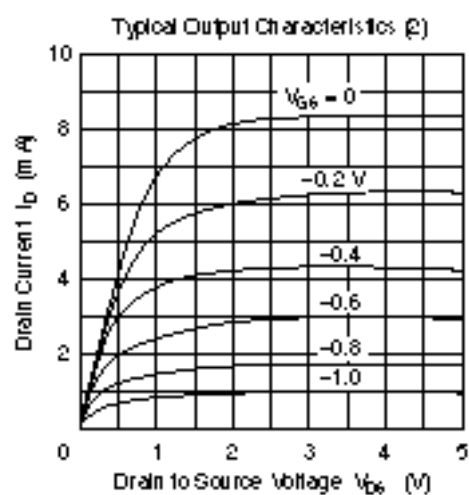
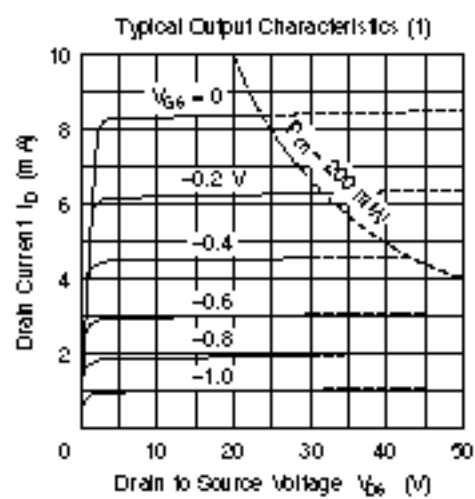
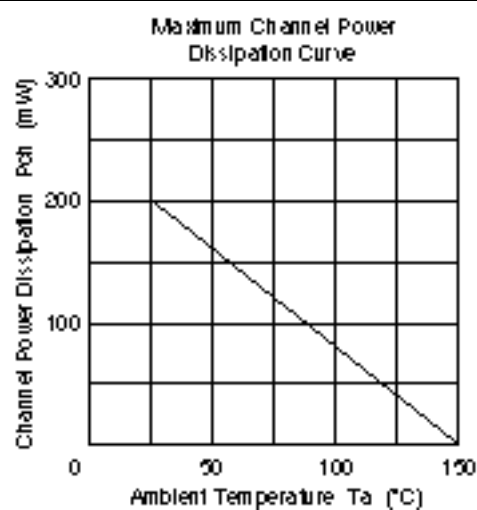
Item	Symbol	Ratings	Unit
Gate to drain voltage	V_{GDO}	-30	V
Gate current	I_G	10	mA
Drain current	I_D	20	mA
Channel power dissipation	Pch	200	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

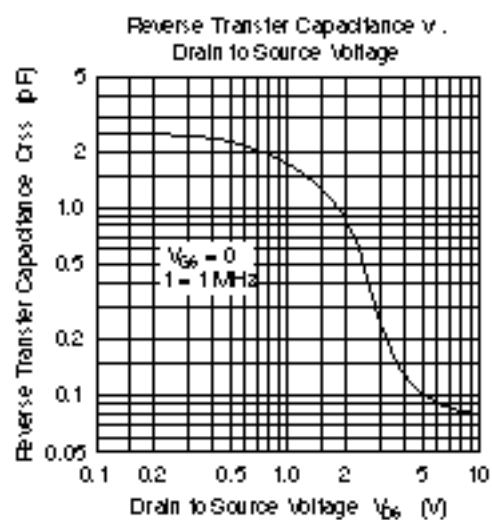
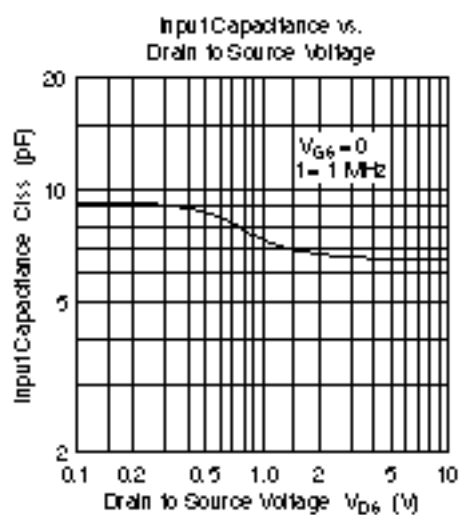
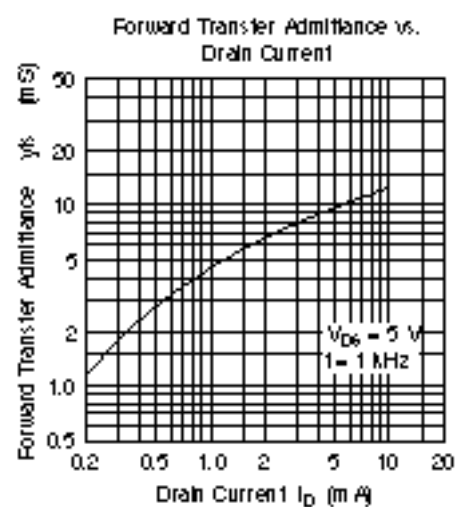
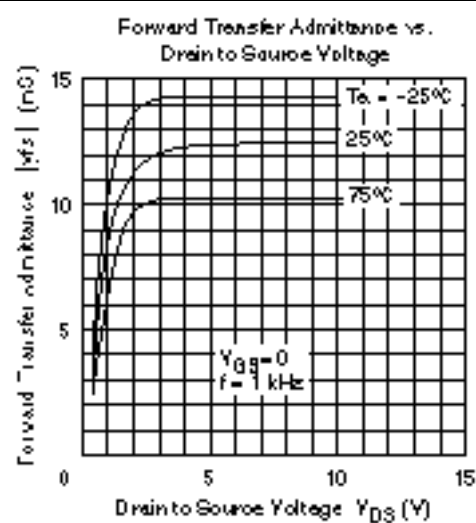
Electrical Characteristics (Ta = 25°C)

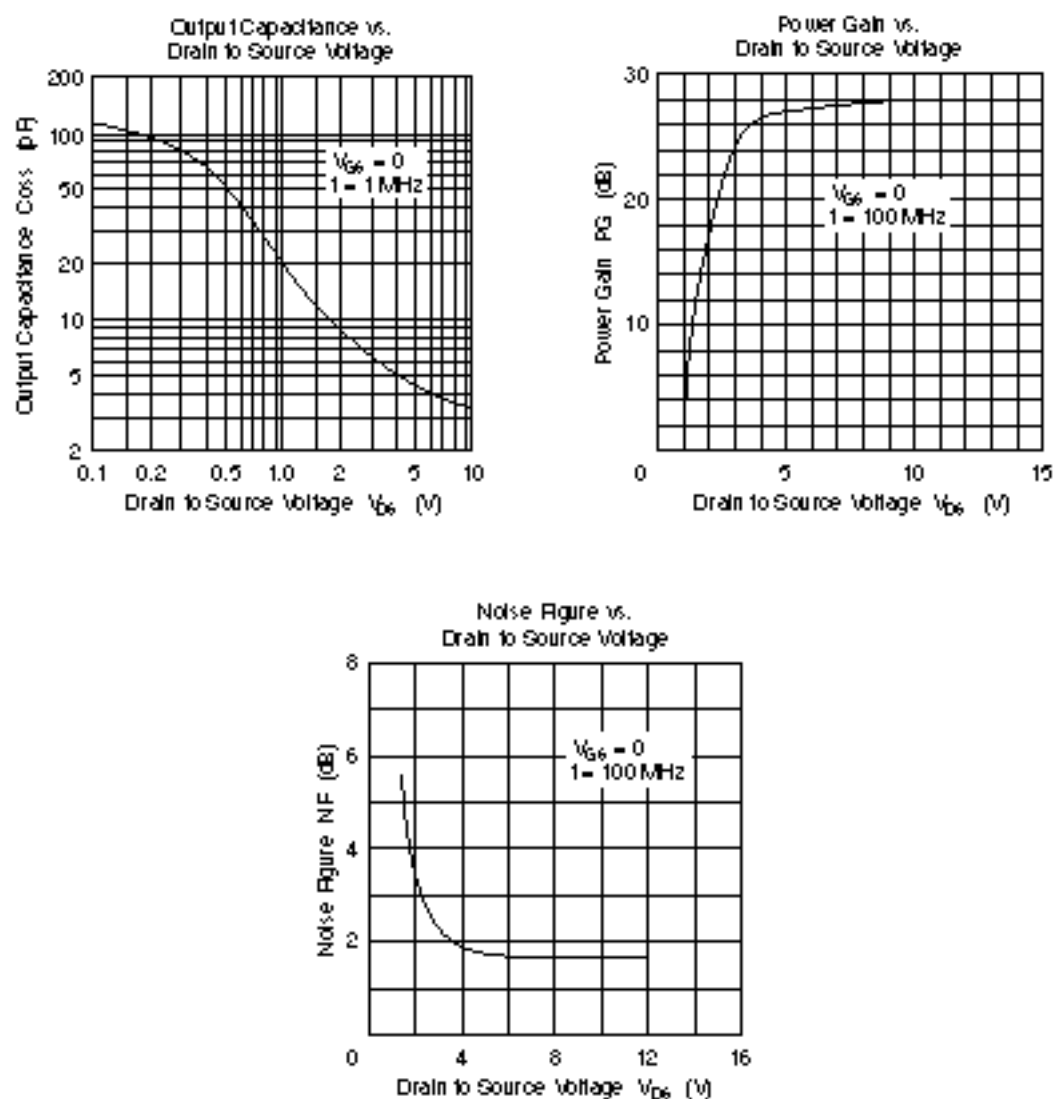
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Gate to drain breakdown voltage	$V_{(BR)GDO}$	-30	—	—	V	$I_G = -100 \mu A$, $I_S = 0$
Gate cutoff current	I_{GSS}	—	—	-10	nA	$V_{GS} = -0.5 V$, $V_{DS} = 0$
Drain current	I_{DSS}^{*1}	4	—	20	mA	$V_{DS} = 5 V$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	—	—	-3	V	$V_{DS} = 5 V$, $I_D = 10 \mu A$
Forward transfer admittance	$ y_{fs} $	8	10	—	mS	$V_{DS} = 5 V$, $V_{GS} = 0$, $f = 1 kHz$
Input capacitance	Ciss	—	6.8	—	pF	$V_{DS} = 5 V$, $V_{GS} = 0$, $f = 1 MHz$
Reverse transfer capacitance	Crss	—	0.1	—	pF	
Power gain	PG	20	27	—	dB	
Noise figure	NF	—	1.7	2.5	dB	$V_{DS} = 5 V$, $V_{GS} = 0$, $f = 100 MHz$

Note: 1. The 2SK522 is grouped by I_{DSS} as follows.

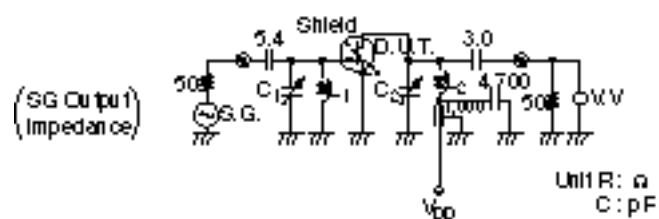
Drain	D	E	F
I_{DSS}	4 to 8	6 to 10	10 to 20







Power Gain and Noise Figure
Test Circuit 1



C_1, C_2 : 0 to 30pF Max Variable Air

L_1 : 3.5 T ϕ 1 mm ϕ Copper Ribbon, Tin plated 10 mm Inside dia.

L_2 : 4.5 T ϕ 1 mm ϕ Copper Ribbon, Tin plated 10 mm Inside dia.

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HITACHI

Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA 94005-4835
U.S.A.
Tel: 415-589-8000
Fax: 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 94 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 0404
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27306074